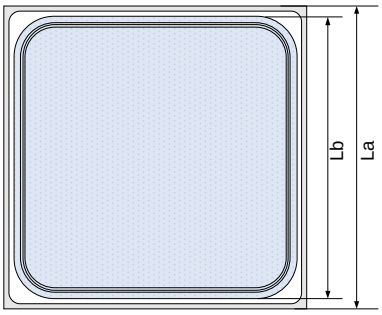
2SB139100MA LOW IR SCHOTTKY BARRIER DIODE CHIPS

DESCRIPTION

- Ø 2SB139100MA is a schottky barrier diode chips fabricated in silicon epitaxial planar technology;
- Ø Due to special schottky barrier structure, the chips have very low reverse leakage current (typical I_R=0.002mA@ Vr=100V) and maximum 150°C operation junction temperature;
- Ø Low power losses, high efficiency;
- Ø Guard ring construction for transient protection;
- Ø High ESD capability;
- Ø High surge capability;
- Ø Packaged products are widely used in switching power suppliers, polarity protection circuits and other electronic circuits;
- Ø Chip Size: 1390μm X 1390μm;
- Ø Chip Thickness: 280±20μm;



Chip Topography and Dimensions

La: Chip Size: 1.390mm;

Lb: Pad Size: 1.295mm;

ORDERING SPECIFICATIONS

Product Name	Specification
2SB139100MAYY	For Axial leads package

ABSOLUTE MAXIMUM RATINGS

Parameters	Symbol	Ratings	Unit
Maximum Repetitive Peak Reverse Voltage	V_{RRM}	100	V
Average Forward Rectified Current	I_{FAV}	3	A
Peak Forward Surge Current@8.3ms	I_{FSM}	80	A
Maximum Operation Junction Temperature	T_J	150	°C
Storage Temperature Range	T_{STG}	-40~150	°C

ELECTRICAL CHARACTERISTICS (T_{amb}=25℃)

Parameters	Symbol	Test Conditions	Min.	Max.	Unit
Reverse Voltage	V_{BR}	I_R=0.5mA	100	--	V
Forward Voltage	V_F	I_F=3A	--	0.85	V
Reverse Current	I_R	V_R=100V	--	0.5	mA